12NS/12NSR

12AMP SILICON POWER DIODE

NSL NAINA

DO-4

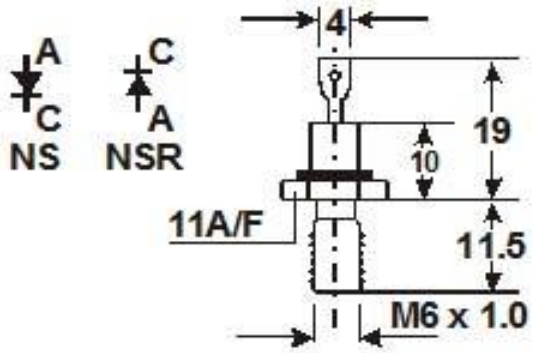
FEATURES

- All Diffused Series
- Available in Normal & Reverse Polarity
- Industrial Grade
- Available In Avalanche Characteristic

ELECTRICAL SPECIFICATIONS

		12NS/NSR
$I_F(A)$	Maximum Average Forward Current Te=150°C	12A
V_{FM}	Maximum peak forward voltage drop @ Rated $I_{F(AV)}$	1.2V
I_{FSM}	Maximum peak one cycle (non-rep) surge current 10msec	250 A
I_{RRM}	Maximum peak one cycle (non -rep) surge current 10msec	60A
I^2t	Maximum I^2t rating (non-rep.) for 5 to 10 m sec.	$250A^2Sec$

12NS/ 12NSR



THERMAL MECHANICAL SPECIFICATIONS

θ_{JC}	Maximum thermal resistance Junction to case	2°C/W
T_J	Operating Junction Temp.	-65°C to 150°C
T_{stg}	Storage temperature	-65°C to 150°C
	Mounting torque (non-lubricated threads)	0.14 M-Kg min, 0.17 M-kg max
W	Approx, weight	7 gms.

ELECTRICAL RATINGS

TYPE	12NS/12NSR	10	20	40	60	80	100	120	140	160
V_{RRM}	Max. repetitive peak voltage (v)	100	200	400	600	800	1000	1200	1400	1600
V_R(RMS)	Max.R.M.S. reversevoltage (V)	70	140	280	420	560	700	840	980	1120
V_R	Max. D.C. Blocking Voltage (V)	100	200	400	60	800	1000	1200	1400	1600
	Recommended R.M.S. working Voltage(v)	40	80	160	240	320	400	480	560	640
I_R(AV)	Max. Average reverse leakage current @ VRMM Tc 25°C uA	100	100	100	100	100	100	100	100	100